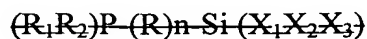


AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A material for forming copper undercoat films comprising a compound ~~represented by the general formula~~



~~characterized in that the compound represented by the general formula is selected from the group consisting of: 1-diethylphosphino-2-triethoxysilylethane, 1-dimethylphosphino-2-trimethoxysilylethane, 1-diethylphosphino-2-trimethoxysilylethane, 1-diphenylphosphino-2-trimethoxysilylethane, 1-dimethylphosphino-3-triethoxysilylpropane, 1-diethylphosphino-3-triethoxysilylpropane, 1-diphenylphosphino-3-triethoxysilylpropane, 1-diphenylphosphino-2-trichlorosilylethane, 1-diphenylphosphino-2-trisdimethylaminosilylethane, 1-diphenylphosphino-2-triisocyanatosilylethane and 1-diphenylphosphino-4-triethoxysilylethylbenzene, wherein the material prevents copper diffusion.~~

2. (Canceled).

3. (Currently Amended) The material for forming copper undercoat films according to claim 1, wherein the alkyl-phosphino-organic-silyl~~(R₁R₂)P-(R)_n-Si~~ groups are capable of bonding~~are bonded~~ to a substrate via Si-O bonding, by a solvent and by the compound ~~represented by the general formula.~~

4. (Canceled).

5. (Withdrawn) A method for forming copper undercoat films comprising, contacting the material for forming copper undercoat films of claim 1 with a substrate surface, thus forming a copper undercoat film.

6. (Withdrawn-Currently Amended) The method for forming copper undercoat films according to claim 5, wherein the undercoat film is produced by the bonding of the alkyl-

phosphino-organic-silyl(R₁R₂)P-(R)_n-Si groups to the substrate via Si-O bonding, and wherein the reaction between the silicon-hydrolytic-Si(X₁X₂X₃) groups and alcohol-OH groups at the substrate surface occurs in liquid phase..

7. (Withdrawn-Currently Amended) The method for forming copper undercoat films according to claim 5, wherein the undercoat film is produced by the bonding of the alkyl-phosphino-organic-silyl(R₁R₂)P-(R)_n-Si groups to the substrate via Si- O bonding, and wherein the reaction between the silicon-hydrolytic-Si(X₁X₂X₃) groups and alcohol-OH groups at the substrate surface occurs in gas phase.

8. (Withdrawn-Currently Amended) The method for forming copper undercoat films according to claim 5, wherein the undercoat film is produced by the bonding of the alkyl-phosphino-organic-silyl(R₁R₂)P-(R)_n-Si groups to the substrate via Si-O bonding, and wherein the reaction between the silicon-hydrolytic-Si(X₁X₂X₃) groups and alcohol-OH groups at the substrate surface occurs in a supercritical liquid.

9. (Withdrawn-Currently Amended) The method for forming copper undercoat films according to claim 5, characterized in that the reaction between the silicon-hydrolytic-Si(X₁X₂X₃) groups and alcohol-OH groups at the substrate surface is carried out under the condition of room temperature to 450 °C.

10. (Canceled).

11. (Canceled).

12. (Withdrawn) A method for forming copper undercoat films comprising, contacting the material for forming copper undercoat films of claim 2 with a substrate surface, thus forming a copper undercoat film.

13. (Withdrawn) The method for forming copper undercoat films according to claim 12, wherein the undercoat film is produced by the bonding of $(R_1R_2)P-(R)_n-Si$ groups to the substrate via Si-O bonding, and wherein the reaction between $-Si(X_1X_2X_3)$ groups and -OH groups at the substrate surface occurs in liquid phase.

14. (Withdrawn) The method for forming copper undercoat films according to claim 12, wherein the undercoat film is produced by the bonding of $(R_1R_2)P-(R)_n-Si$ groups to the substrate via Si-O bonding, and wherein the reaction between $-Si(X_1X_2X_3)$ groups and -OH groups at the substrate surface occurs in gas phase.

15. (Withdrawn) The method for forming copper undercoat films according to claim 12, wherein the undercoat film is produced by the bonding of $(R_1R_2)-(R)_n-Si$ groups to the substrate via Si-O bonding, and wherein the reaction between $-Si(X_1X_2X_3)$ groups and -OH groups at the substrate surface occurs in a supercritical liquid.

16. (Withdrawn) The method for forming copper undercoat films according to claim 12, characterized in that the reaction between $-Si(X_1X_2X_3)$ groups and -OH groups at the substrate surface is carried out under the condition of room temperature to 450 °C.